

## METHOD FOR GROWING III-V COMPOUND SEMICONDUCTOR CRYSTAL ON SI SUBSTRATE

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Patent Number: JP1009896  
Publication date: 1989-01-13  
Inventor(s): MATSUMOTO TAKU  
Applicant(s): NEC CORP  
Requested Patent: ☐ JP1009896  
Application Number: JP19870165695 19870701  
Priority Number(s):  
IPC Classification: C30B29/40; C30B25/14  
EC Classification:  
EC Classification:  
Equivalents:

### Abstract

**PURPOSE:** To grow the titled superconductor crystal, having good crystallinity and capable of selective growth on a substrate, by alternately feeding a gas species containing Ga chloride and a gas species containing group V constituent element onto a silicon substrate having a formed mask pattern.

**CONSTITUTION:** A Ga source boat 12 is placed on the upstream side of a growth chamber 11 in the lower stage and a carrier gas and HCl gas are fed from the upstream side thereof to adsorb the formed Ga chloride on a silicon substrate 14 having a formed mask pattern. The substrate 14 is then moved to a growth chamber 13 in the upper stage and a gas species containing a group V constituent element is fed and adsorbed on the substrate 14. The above-mentioned operations are alternately repeated to carry out atomic layer epitaxial growth of a III-V compound semiconductor crystal on the substrate 14.